



# Thermal transport from first-principles DFT calculations

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# Classical MD simulations ...

- ... use an empirical potential fitted to reproduce lattice constant, cohesive energy, elastic properties, some phonons...
- But are not supposed to produce correct third derivatives of the potential energy, determining phonon lifetimes
- They can be used to explain **trends** in thermal transport, but can not **predict quantitatively** the thermal conductivity.

# Goal

- To develop a general methodology to get **accurate** estimates of thermal properties using available density functional theory (DFT) tools.
- To make accurate / reliable predictions without fitting any parameters to experimental data.

# Outline

- New force field based on FP-DFT
- Approaches for thermal conductivity calculation + illustrations
  - Lattice dynamics model
  - MD
  - Green's functions for coherent transport
- Conclusions

# Force field model

Force      displacements

$$-\mathbf{F}_i^\alpha = \nabla_i^\alpha E = \Pi_i^\alpha + \sum_{j,\beta} \Phi_{ij}^{\alpha\beta} u_j^\beta + \frac{1}{2!} \sum_{jk,\beta\gamma} \Psi_{ijk}^{\alpha\beta\gamma} u_j^\beta u_k^\gamma$$

$$+ \frac{1}{3!} \sum_{jkl,\beta\gamma\delta} X_{ijkl}^{\alpha\beta\gamma\delta} u_j^\beta u_k^\gamma u_l^\delta$$

$$\Pi_i^\alpha = \frac{\partial E}{\partial u_i^\alpha}; \quad \Phi_{ij}^{\alpha\beta} = \frac{\partial^2 E}{\partial u_i^\alpha \partial u_j^\beta}; \quad \Psi_{ijk}^{\alpha\beta\gamma} = \frac{\partial^3 E}{\partial u_i^\alpha \partial u_j^\beta \partial u_k^\gamma};$$

$$X_{ijkl}^{\alpha\beta\gamma\delta} = \frac{\partial^4 E}{\partial u_i^\alpha \partial u_j^\beta \partial u_k^\gamma \partial u_l^\delta}$$

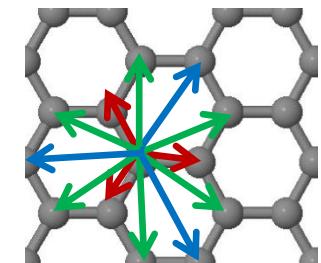
Derivatives are calculated at or near equilibrium  
**Exact for small displacements!**

As the FCs are 2<sup>nd</sup> or higher rank tensors,  
there are a **huge** number of terms in the  
Taylor expansion!

9 for each pair \* number of pairs

27 for each triplet \* number of triplets

81 for each quadruplet \* number of quadruplets



# They need to be reduced

Method to extract anharmonic force constants from first principles calculations

Keivan Esfarjani and Harold T. Stokes  
Phys. Rev. B **77**, 144112 (2008)

# Symmetry constraints

The FCs are related by the following symmetry constraints:

- Permutation of the order of derivatives

$$\Phi_{ij}^{\alpha\beta} = \Phi_{ji}^{\beta\alpha}$$

- Global Translational invariance

$$0 = \sum_j \Phi_{ij}^{\alpha\beta} ; 0 = \sum_j \Psi_{ijk}^{\alpha\beta\gamma}$$

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# Symmetry constraints

- Global Rotational invariance

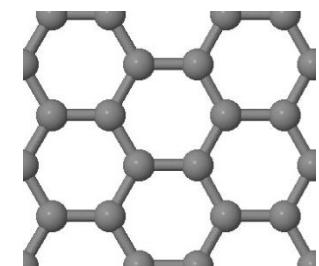
Links FCs to higher-order ones

$$\sum_R \Psi \times R = \Phi ; \sum_R X \times R = \Psi$$

- Group symmetry operation invariance

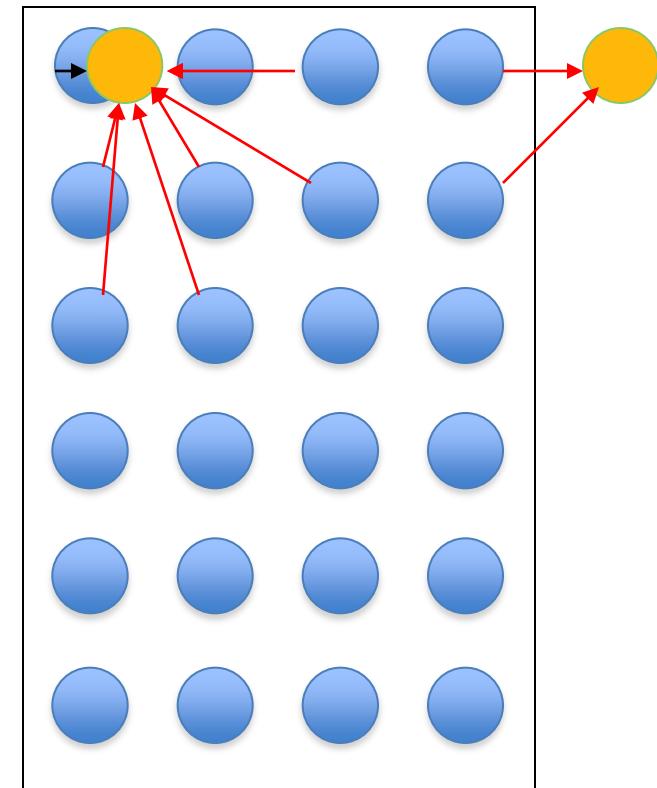
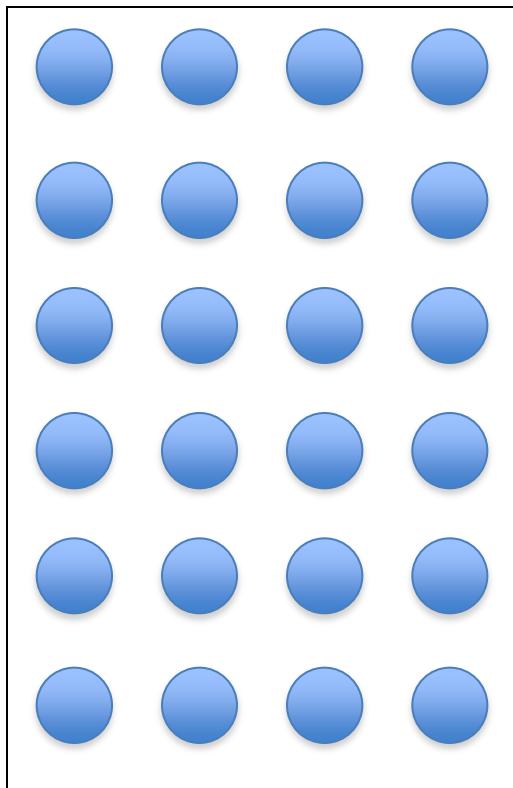
$$\Phi_{ij}^{\alpha\beta} = \sum_{\alpha'\beta'} S_{\alpha\alpha'} S_{\beta\beta'} \Phi_{S(i)S(j)}^{\alpha'\beta'}$$

...



These symmetries **must be enforced** for any  
FC model to be **physically correct**

# Methodology : FP-DFT calculations in a supercell (real space)



**Supercell size should ideally be larger than the range of the force constants**

$$-F_i^\alpha = \Pi_i^\alpha + \sum_{j,\beta} \Phi_{ij}^{\alpha\beta} u_j^\beta + \frac{1}{2!} \sum_{jk,\beta\gamma} \Psi_{ijk}^{\alpha\beta\gamma} u_j^\beta u_k^\gamma + \dots$$

# Extraction of FCs:

- Constraints are **linear** in FCs
- Force-displacement relations **also linear** in FCs

$$\boxed{\begin{array}{c} \text{Invariance constraints} \\ U \end{array}} \boxed{\begin{array}{c} \Phi \\ = \end{array}} \boxed{\begin{array}{c} 0 \\ F \\ \text{FP-DFT Force-displacement data} \end{array}}$$

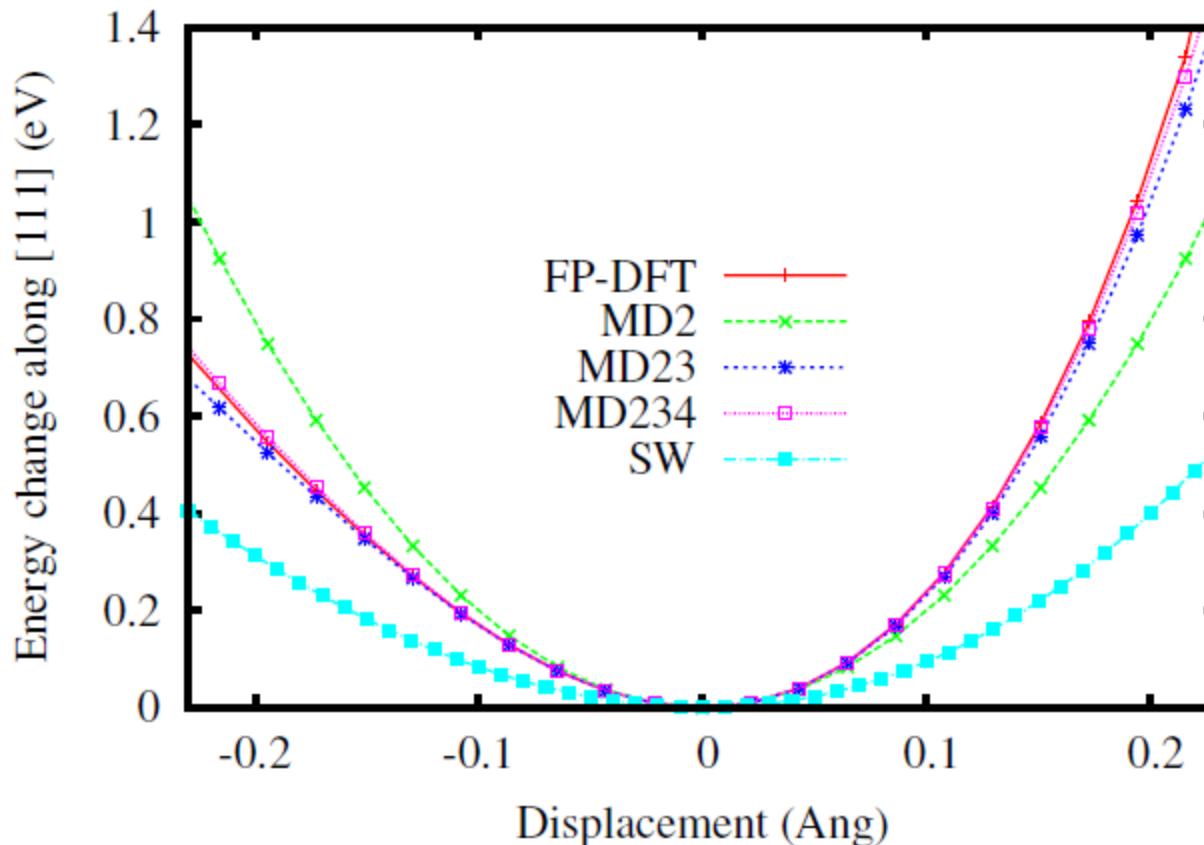
- Over-complete system of linear equations
- FCs are deduced from a **SVD algorithm**

Method to extract anharmonic force constants from first principles calculations

Keivan Esfarjani and Harold T. Stokes, Phys. Rev. B **77**, 144112 (2008)

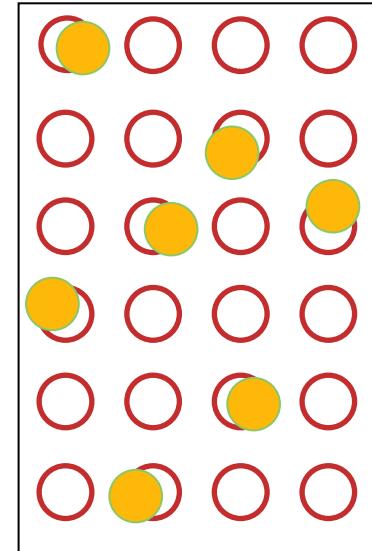
# How accurate are the obtained FCs?

- Move one Si atom along [111]



# More validation

- Use the FCs to calculate forces for arbitrary atomic displacements



	Denominator	$\sigma(\text{Poly})$	$\sigma(\text{SW})$
DISP=0.1 Ang	205.67	0.046941	0.34490
DISP=0.2 Ang	1166.9	0.082234	0.28324



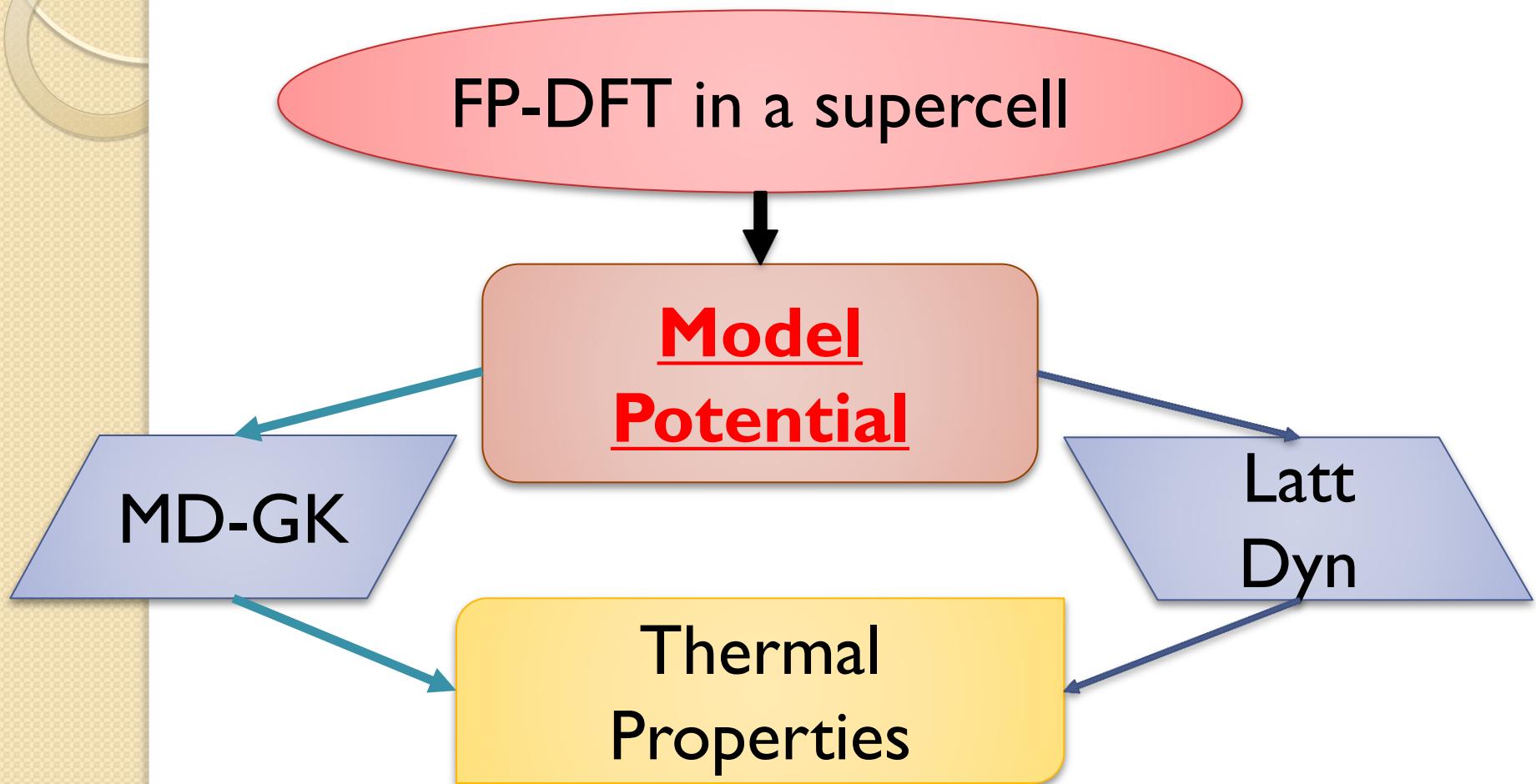
Error is due to choosing (5,1,1) neighbors in the model

# Now what ?

- Use second derivatives to get phonon dispersion
- Use the third derivatives to get phonon lifetimes
- Use all to do MD

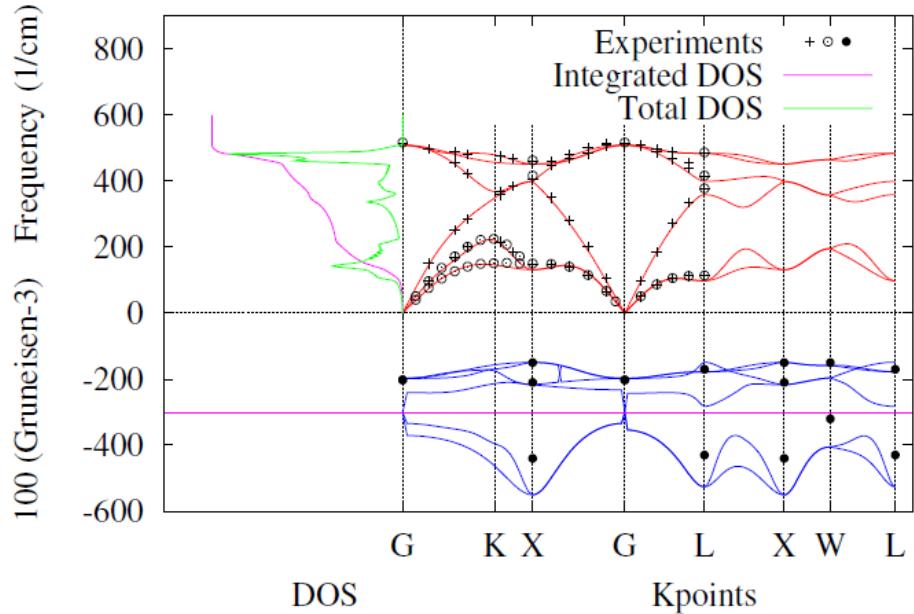
Alternative approach to determining FCs uses  
DFPT  
(See talk by Derek Stewart)

# Summary of the approach



# Phonon Dispersion For Si, Graphene, ZrCoSb

Band Structure and DOS for Si

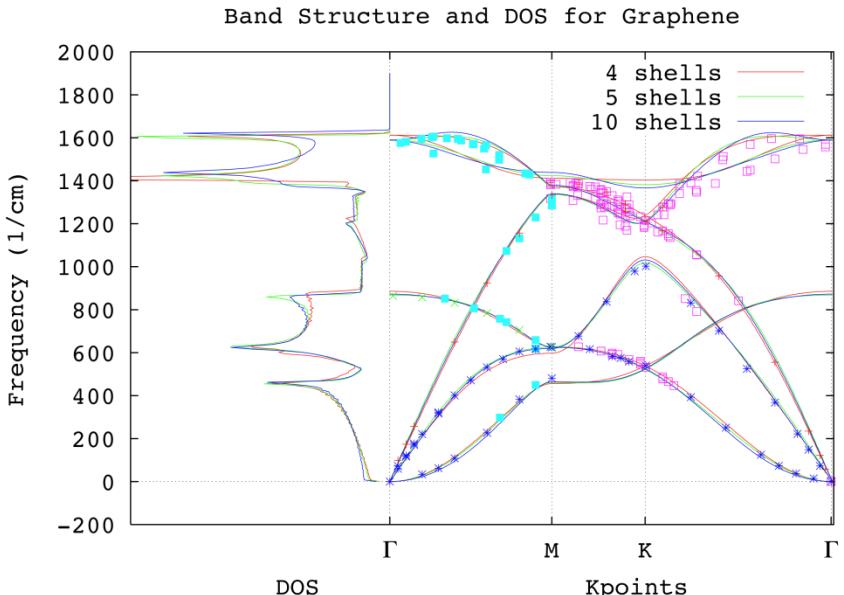


K. Esfarjani, G. Chen, and H.T. Stokes  
Phys. Rev. B **84**, 085204 (2011)

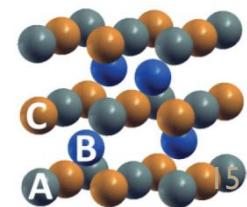
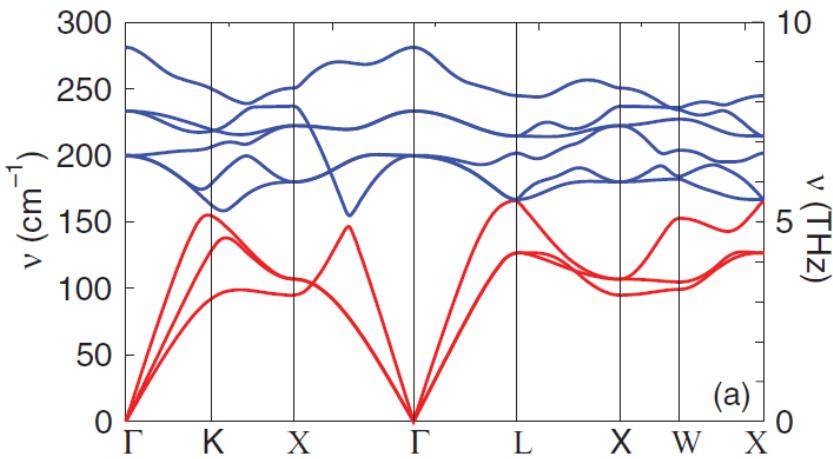
$$\gamma_{k\lambda} = -\frac{d \ln \omega_{k\lambda}}{d \ln V}$$

ZrCoSb Half-heusler; By J. Shiomi, KE, G. Chen, PRB 84 (2011)

5/23/2012

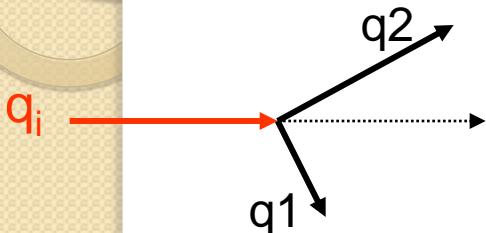


N. Mingo, K. Esfarjani, D.A. Broido, and D.A. Stewart  
Phys. Rev. B **81**, 045408 (2010)

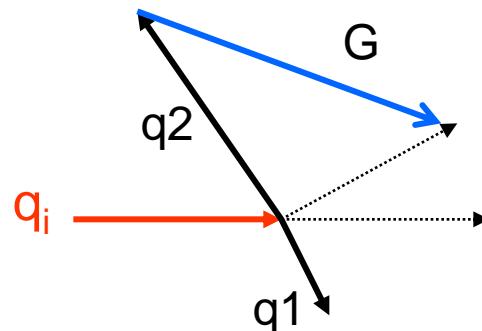


Phonon School @ UWM

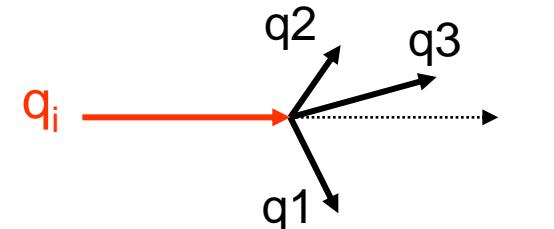
# Lifetimes due to 3-phonon processes



Normal process

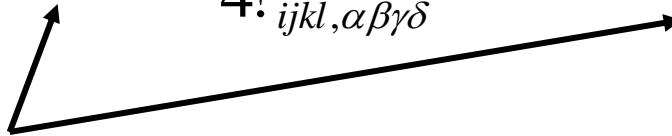


Umklapp process



a 4-phonon process

$$V = \frac{1}{3!} \sum_{ijk, \alpha\beta\gamma} \Psi_{ijk}^{\alpha\beta\gamma} u_i^\alpha u_j^\beta u_k^\gamma + \frac{1}{4!} \sum_{ijkl, \alpha\beta\gamma\delta} X_{ijkl}^{\alpha\beta\gamma\delta} u_i^\alpha u_j^\beta u_k^\gamma u_l^\delta + \dots$$



Phonon creation and annihilation operators

$$W(i, f) = \frac{2\pi}{\hbar} | \langle i | V | f \rangle |^2 \delta(E_i - E_f) \quad \text{Fermi Golden Rule}$$

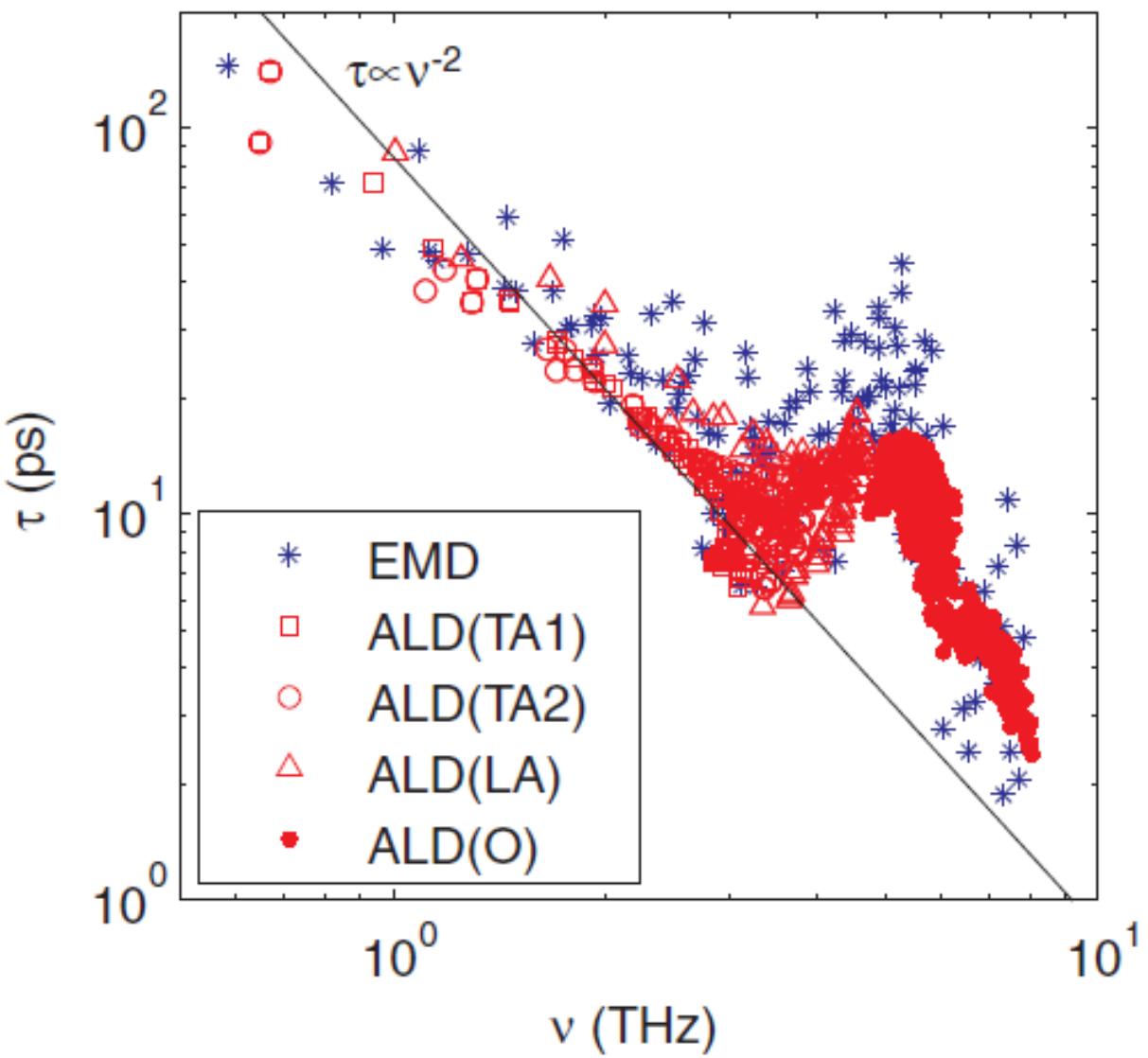
# Thermal conductivity

- Use of the relaxation time approximation

$$\kappa = \frac{1}{3} \sum_{k\lambda} v_{k\lambda}^2 \tau_{k\lambda} \hbar \omega_{k\lambda} \partial n_{k\lambda} / \partial T$$

Relaxation time      C<sub>v</sub> per mode

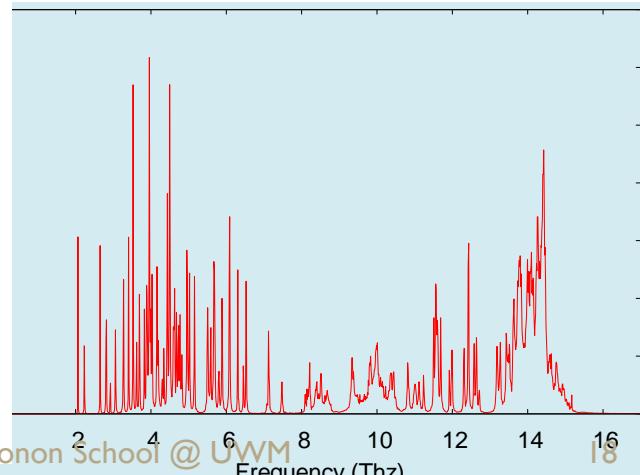
# ZrCoSb lifetimes: LD-FGR versus MD



Shiomi, Esfarjani, Chen, Phys. Rev. B 84, 104302 (2011)



$$E(\nu) = \left\langle \sum_{\alpha\eta l} M_\eta \left| \int v_{\eta l}^\alpha(t) e^{-2\pi i \nu t} dt \right|^2 \right\rangle,$$

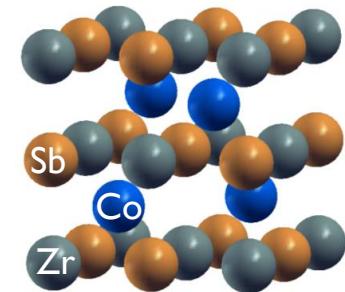
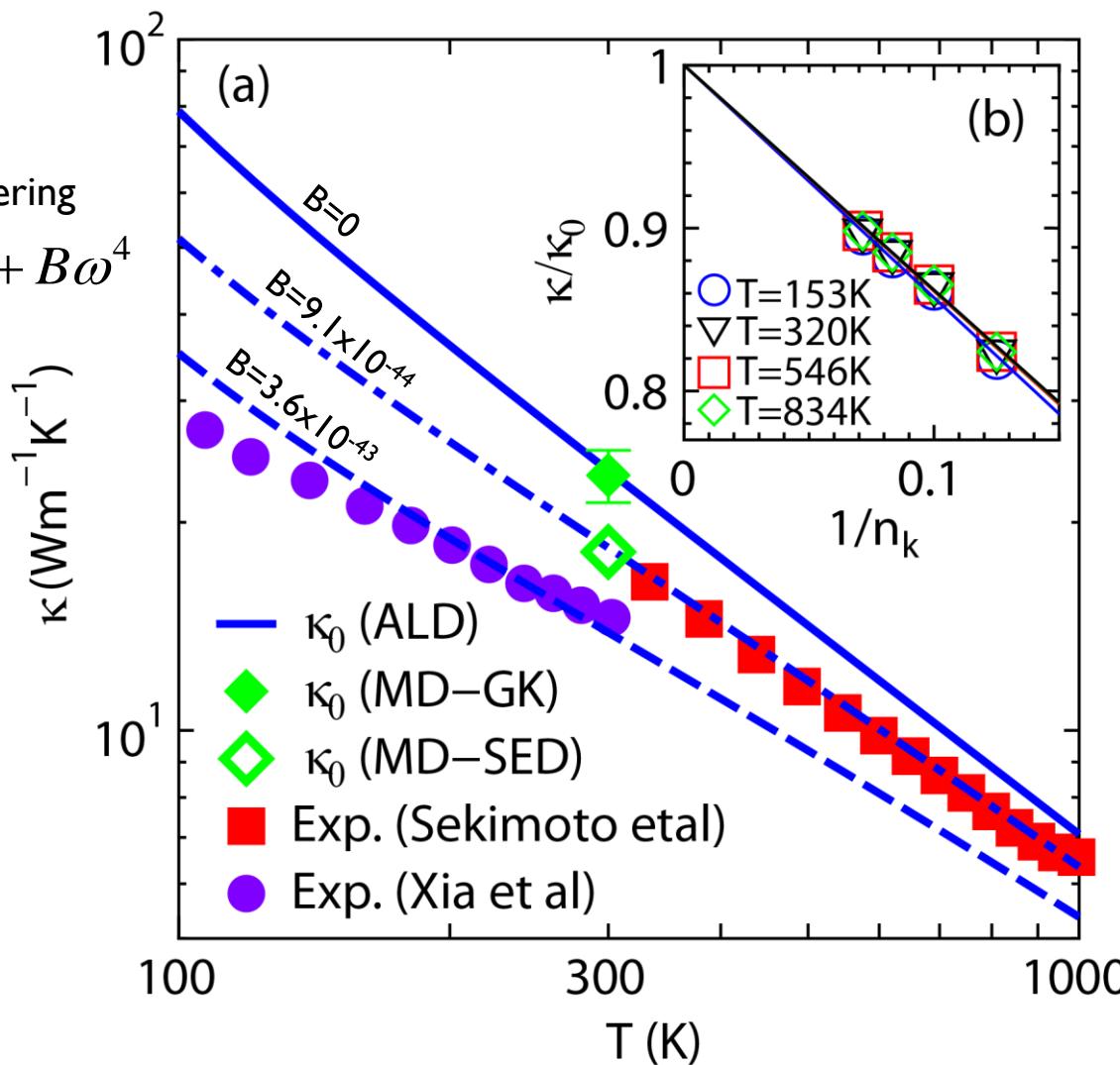


# Thermal conductivity of ZrCoSb

## Simulations vs Experiments

Impurity scattering

$$1/\tau = 1/\tau_0 + B\omega^4$$



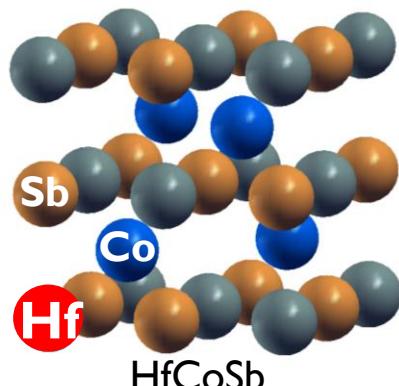
# Alloying effect on half-Heusler thermal conductivity

Transferability of force constants

$22 \text{ Wm}^{-1}\text{K}^{-1}$

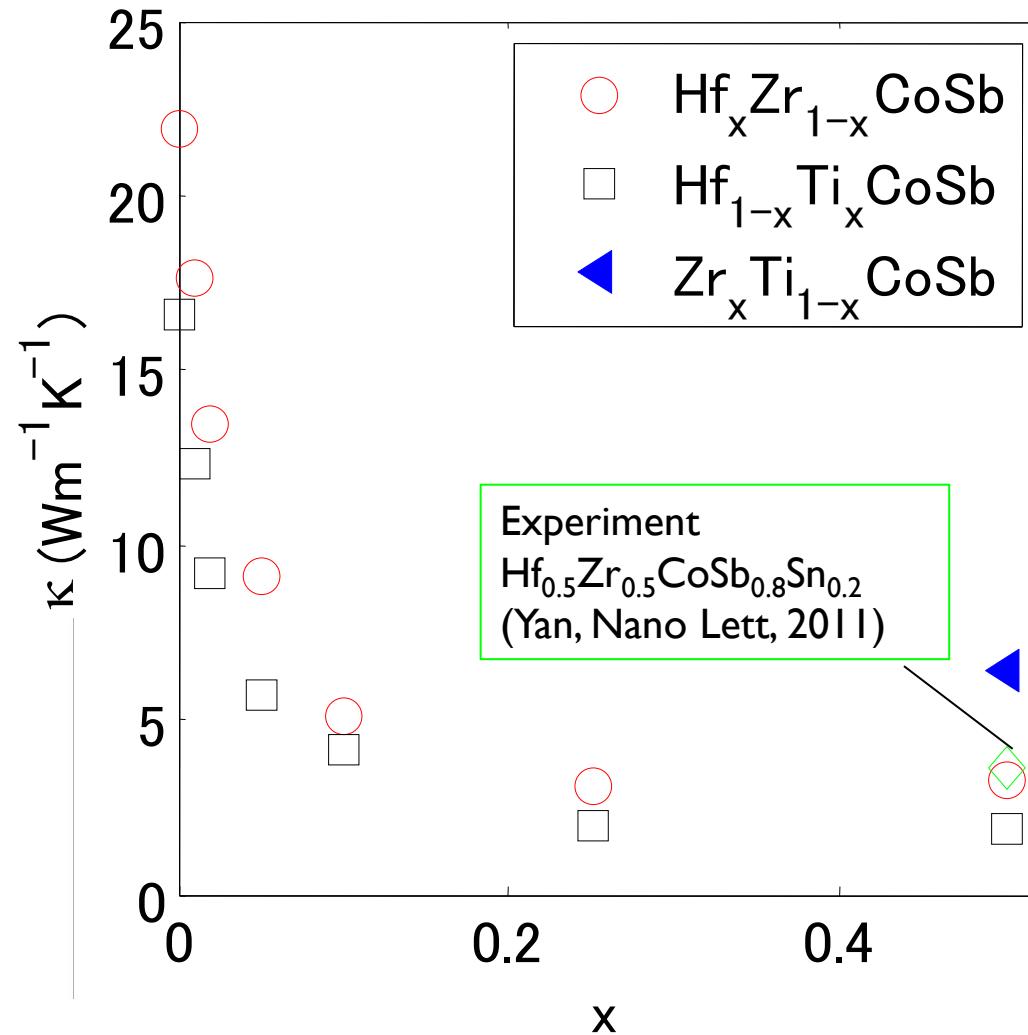


Only changing mass



$16 \text{ Wm}^{-1}\text{K}^{-1}$

Green Kubo Calculation (300 K)



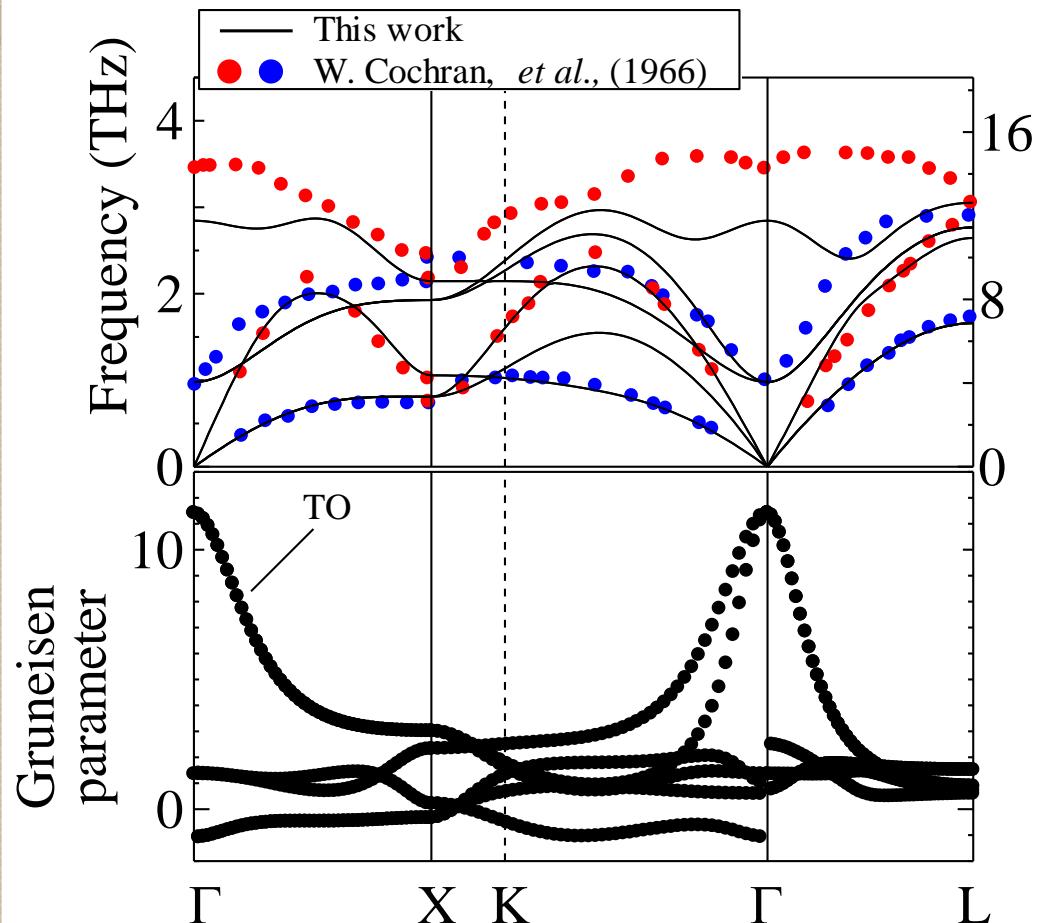
# Thermal conductivity of PbTe

Microscopic mechanism of low thermal conductivity in lead telluride

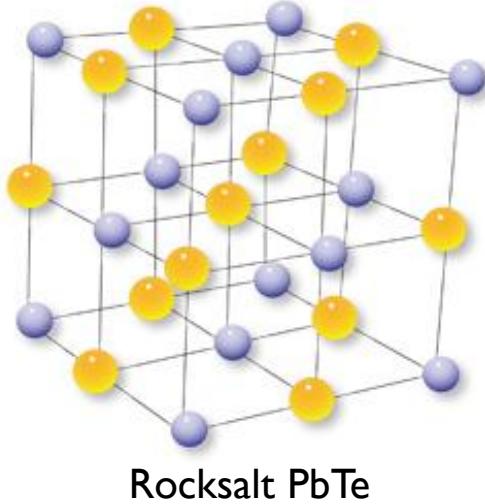
T Shiga, J Shiomi, J Ma, O Delaire, T Radzynski, A Lusakowski, K E, and G Chen  
Phys. Rev. B **85**, 155203 (2012)



Takuma Shiga



Why is thermal conductivity  
of PbTe so low  
(~ $2 \text{ Wm}^{-1}\text{K}^{-1}$  @300K)?



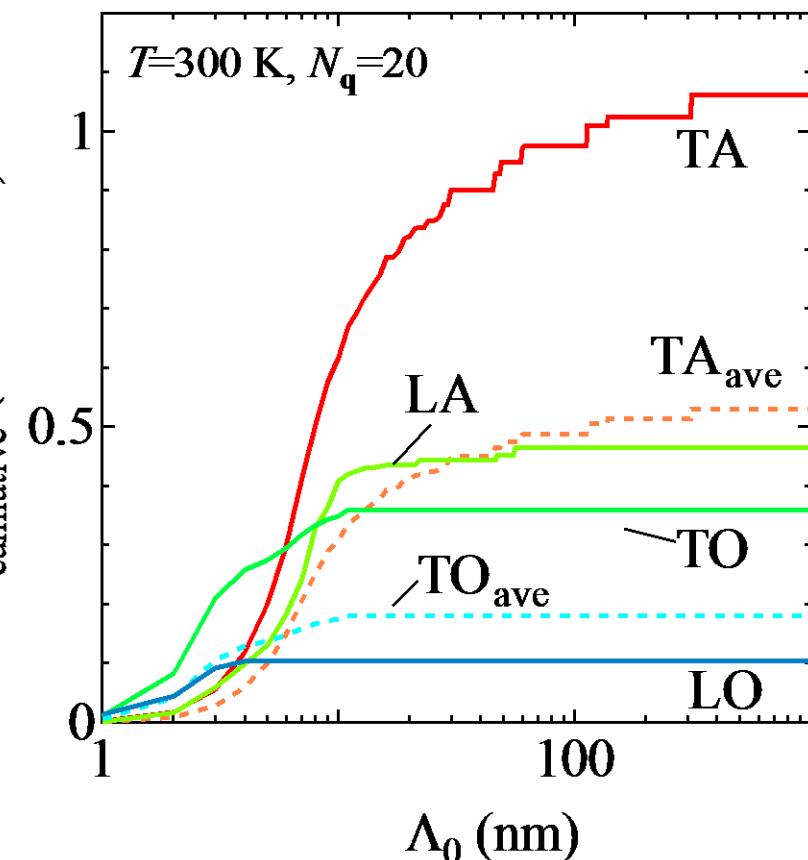
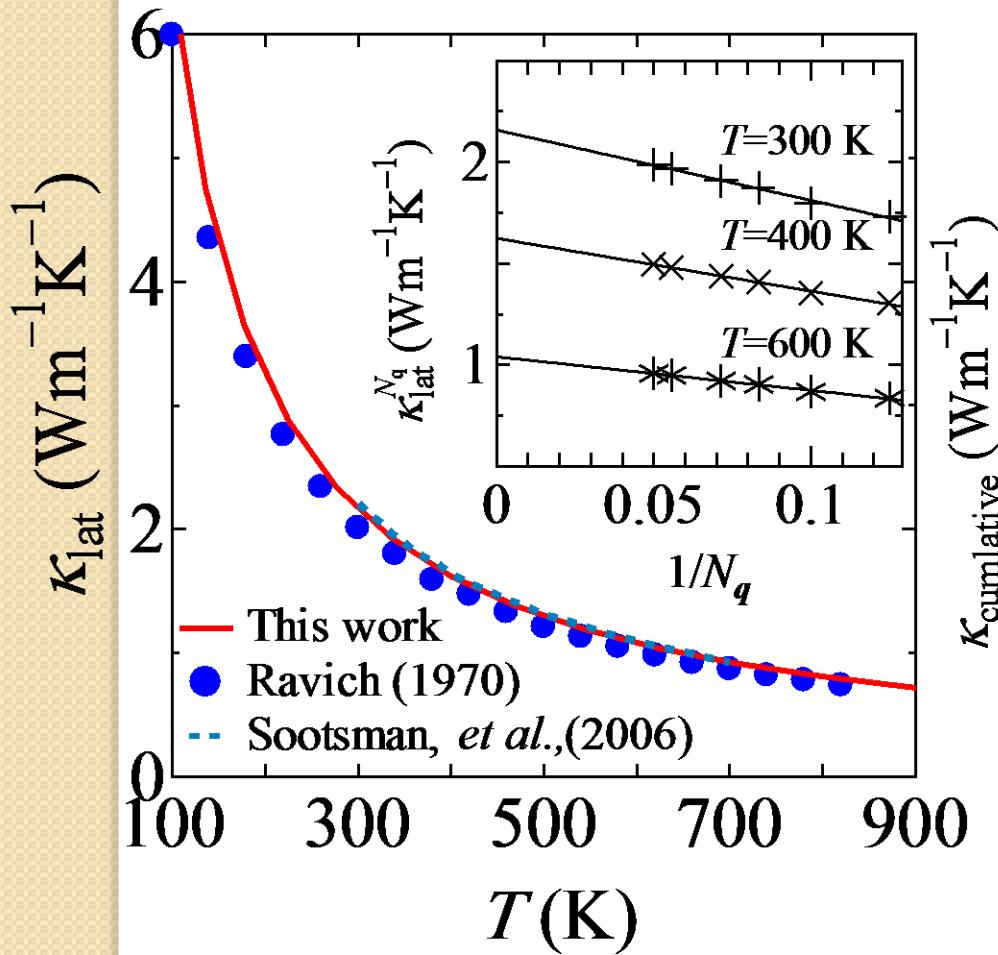
# Phonons in lead telluride

Microscopic mechanism of low thermal conductivity in lead telluride

T Shiga, J Shiomi, J Ma, O Delaire, T Radzynski, A Lusakowski, K E, and G Chen  
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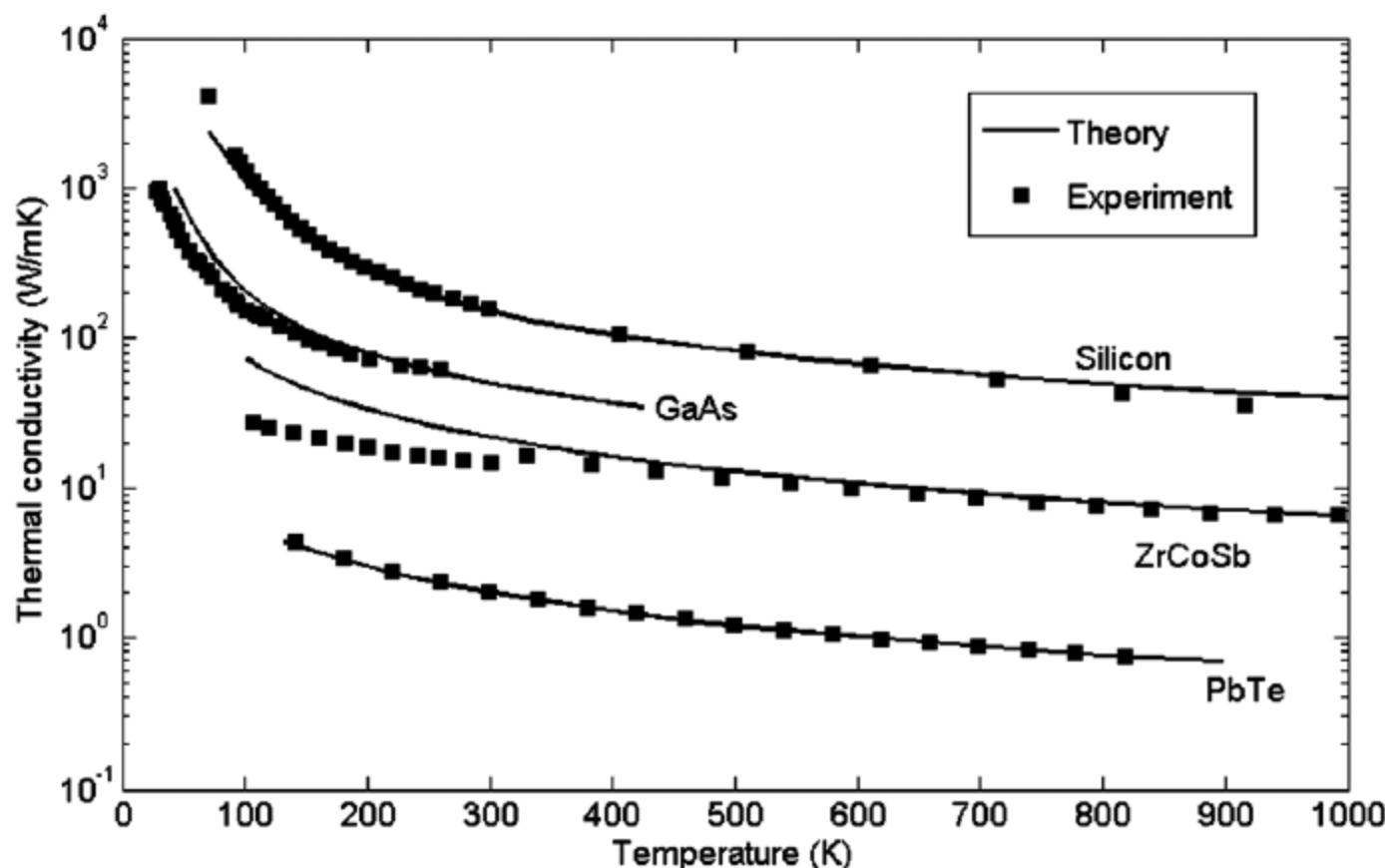
Takuma Shiga



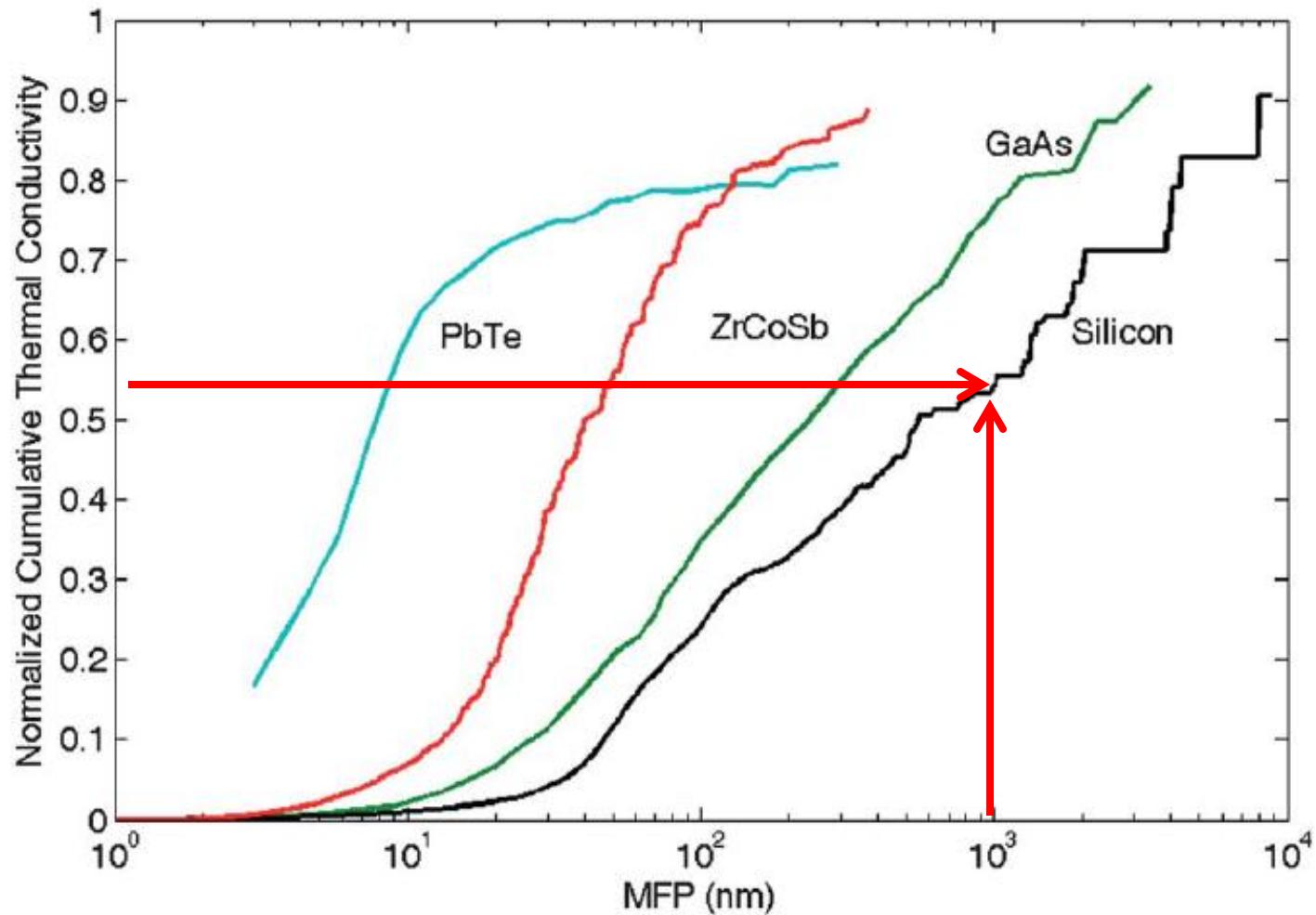
# Perspectives on thermoelectrics: from fundamentals to device applications

M. Zebarjadi,<sup>a</sup> K. Esfarjani,<sup>a</sup> M. S. Dresselhaus,<sup>b</sup> Z. F. Ren<sup>\*c</sup> and G. Chen<sup>\*a</sup>

*Energy Environ. Sci.*, 2012, **5**, 5147



# Summary of LD: MFP distribution



Perspectives on thermoelectrics: from fundamentals to device applications

M. Zebarjadi,<sup>a</sup> K. Esfarjani,<sup>a</sup> M. S. Dresselhaus,<sup>b</sup> Z. F. Ren<sup>\*c</sup> and G. Chen<sup>\*a</sup>

Energy Environ. Sci., 2012, 5, 5147

Phonon School @ UWM

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# MD using the polynomial force field

- PROS:

- Of accuracy similar to DFT
- Includes anharmonic effects to higher order

- CONS:

- Can not describe structural changes
- Hard to include surfaces and defects
- Ideal for thermal conductivity using GK

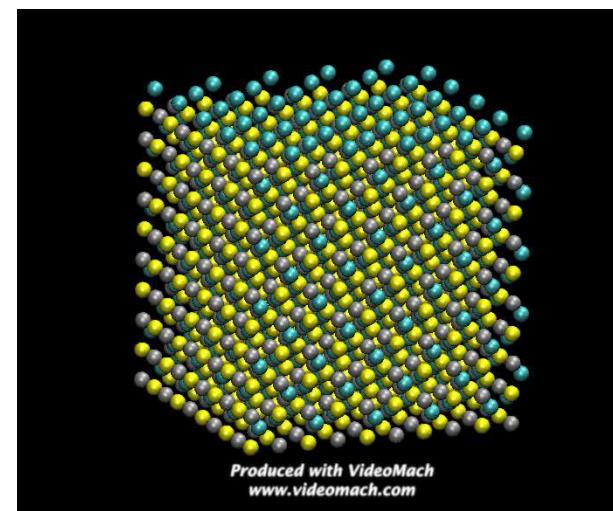
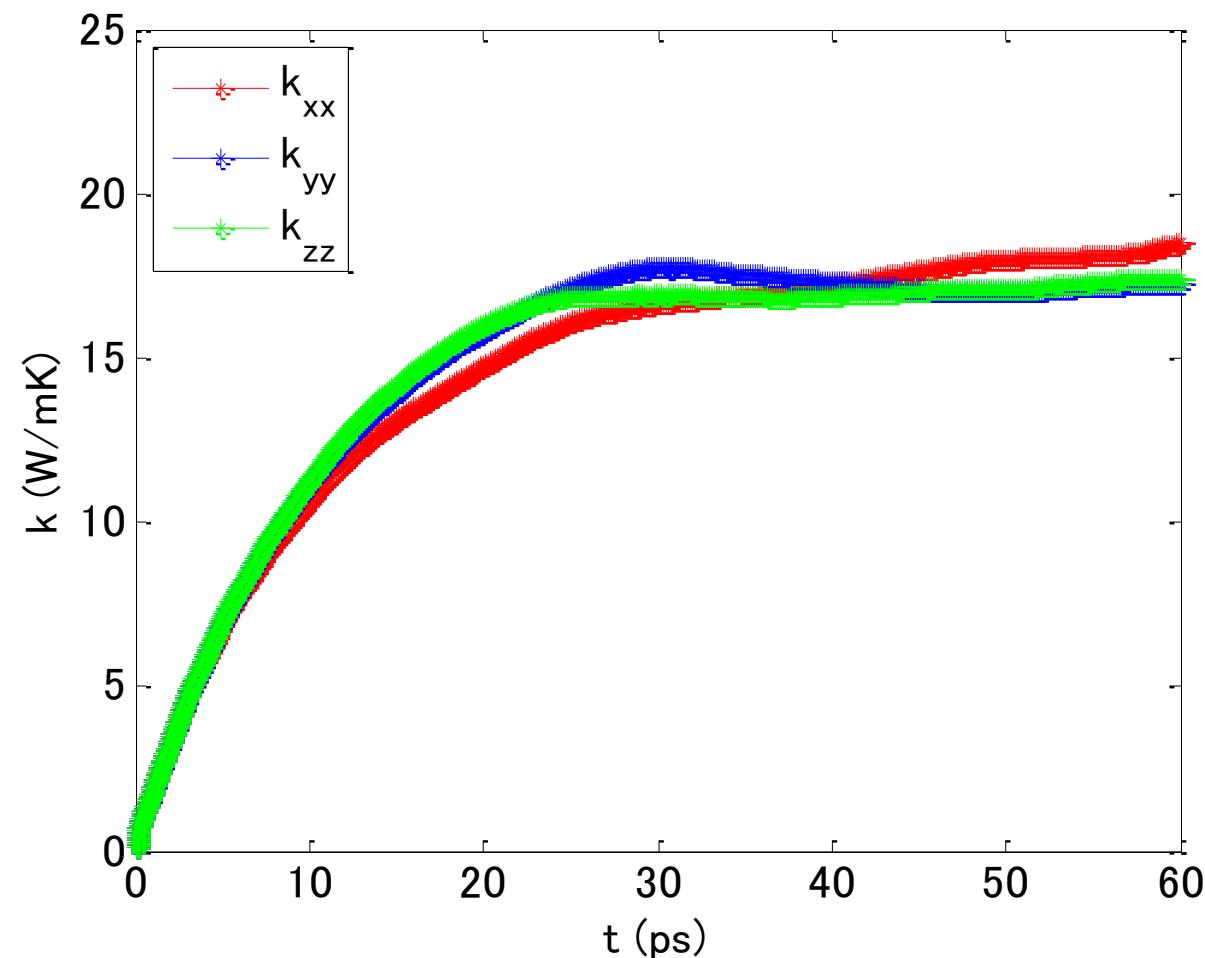
# Equilibrium Green-Kubo (GK)

$$\kappa_{\alpha\beta} = \frac{1}{V k_B T^2} \int_0^\infty \langle J^\alpha(0) J^\beta(t) \rangle dt$$

$$J^\alpha = \sum_i J_i^\alpha = \sum_i \frac{d(e_i r_i^\alpha)}{dt} = \sum_{ij} (R_i^\alpha - R_j^\alpha) (v_j \cdot \frac{\partial e_i}{\partial u_j})$$

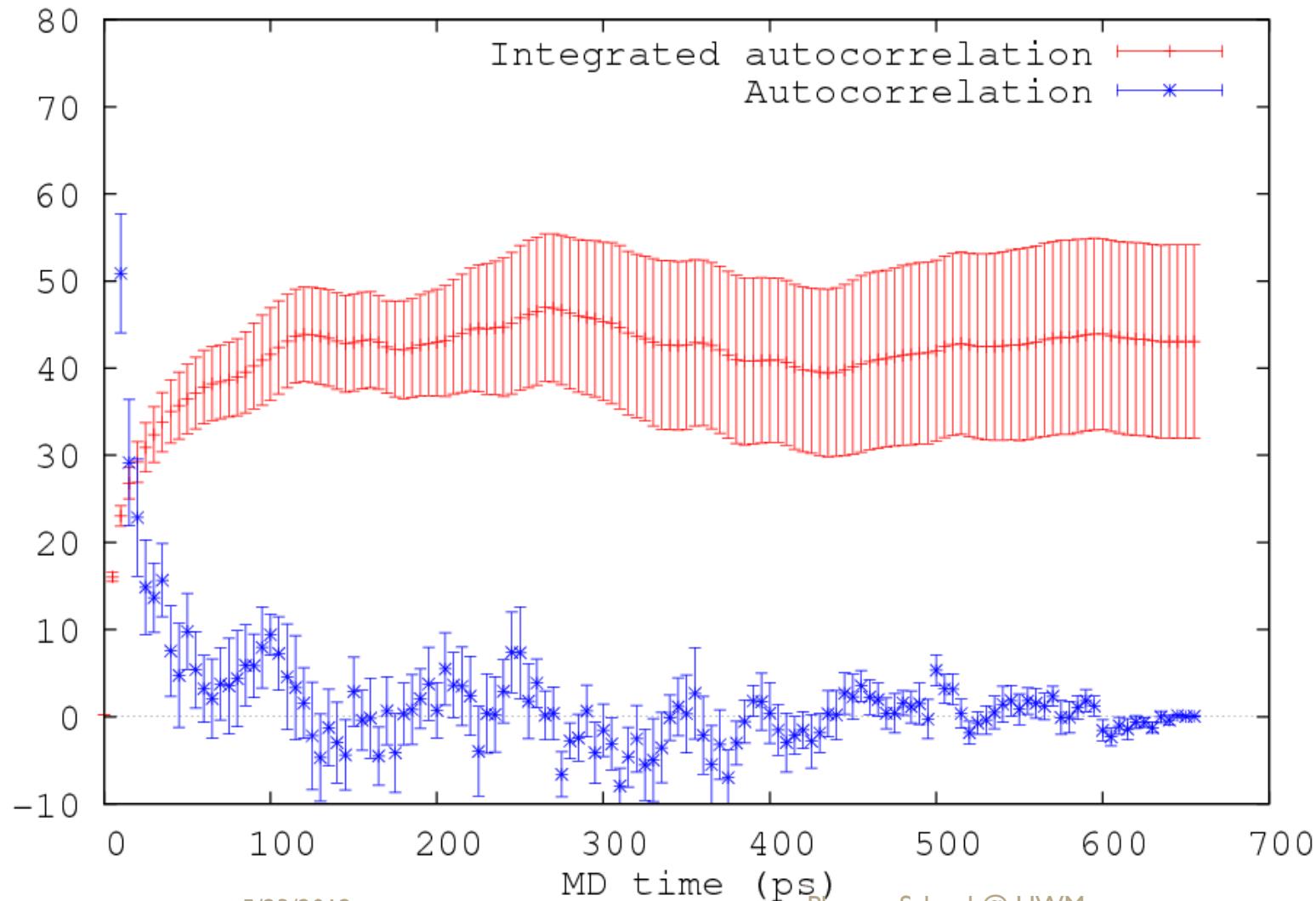
$$\begin{aligned} e_i &= \frac{1}{2} m_i v_i^2 + \frac{u_i}{2} \sum_j [\Phi_{ij} u_j + \frac{1}{3} \sum_k \Psi_{ijk} u_j u_k \\ &+ \frac{1}{12} \sum_{ijkl} \chi_{ijkl} u_j u_k u_l] \end{aligned}$$

# Half-Heuslers



# Silicon

Autocorrelation and its cumulative integral (10x10x10)



# Wave effects in thermal transport

- Quantization of thermal conductance
- Coherent (ballistic) phonon contribution

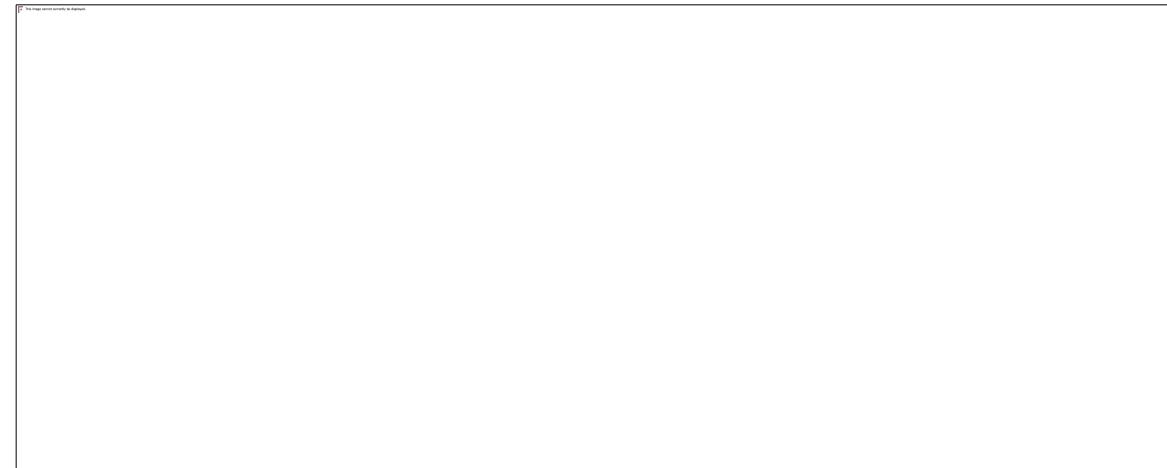
# Coherent phonon transport

- Landauer formula

$$G = \sum_m \int_0^{\infty} \frac{d\omega}{2\pi} \boxed{D_m(\omega) v_{gm}} \hbar\omega \frac{\partial n(T, \omega)}{\partial T} \Xi(\omega)$$

- Transmission formula

= 1





# Experimental samples

9 periods

7 periods

5 periods

3 periods

1 period

$\sim 100$  nm Al

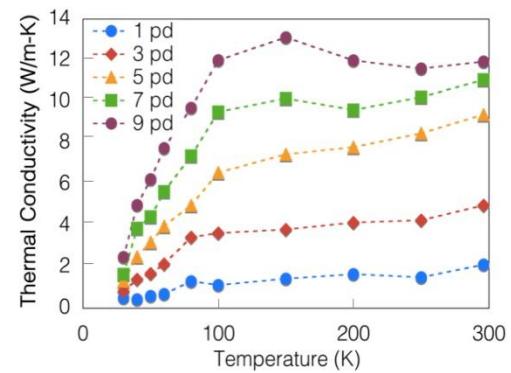
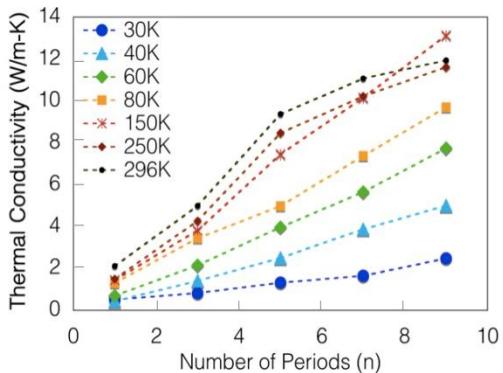
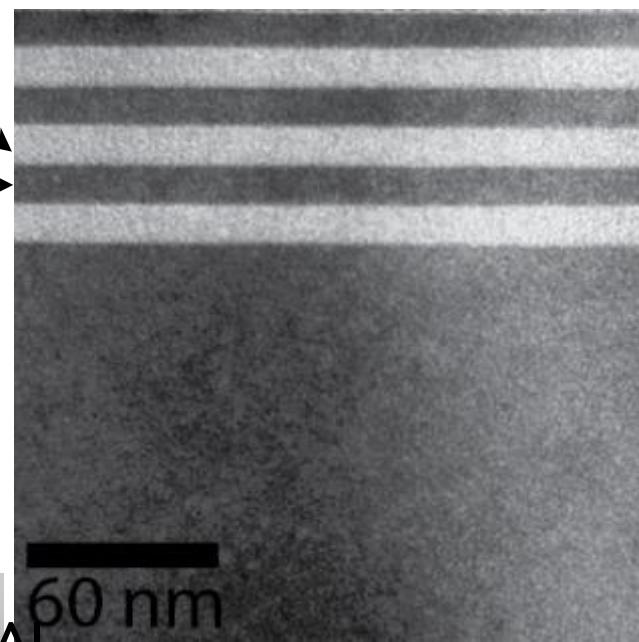
60 nm

12 nm GaAs  
12 nm AlAs

350 $\mu$ m GaAs

12 nm AlAs

12 nm GaAs



# $\text{GaAs}-[(\text{AlAs})_{22}/(\text{GaAs})_{22}]_{N=1,\dots,9}-\text{Al}$

GaAs

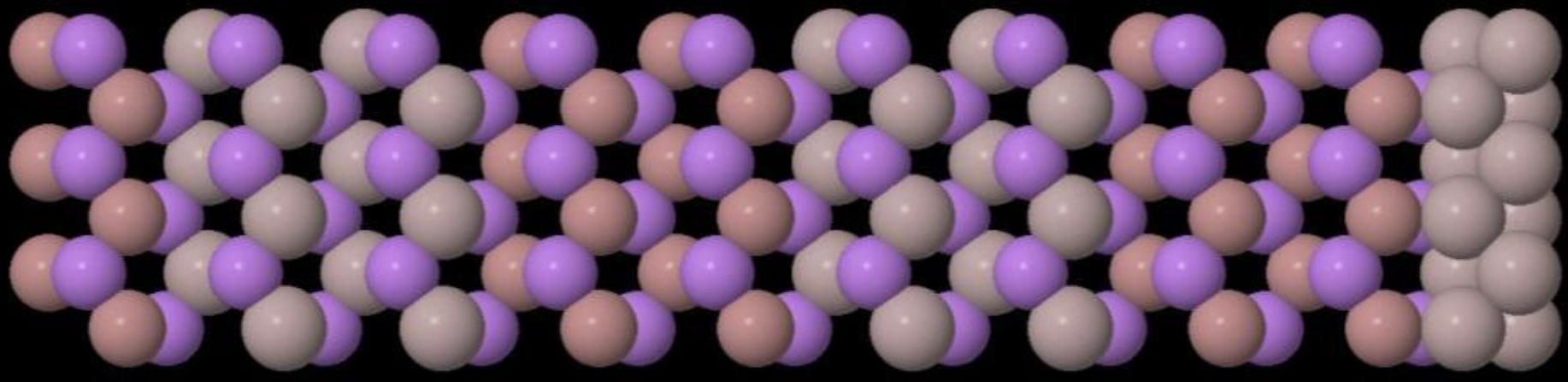
AlAs

GaAs

AlAs

GaAs

Al

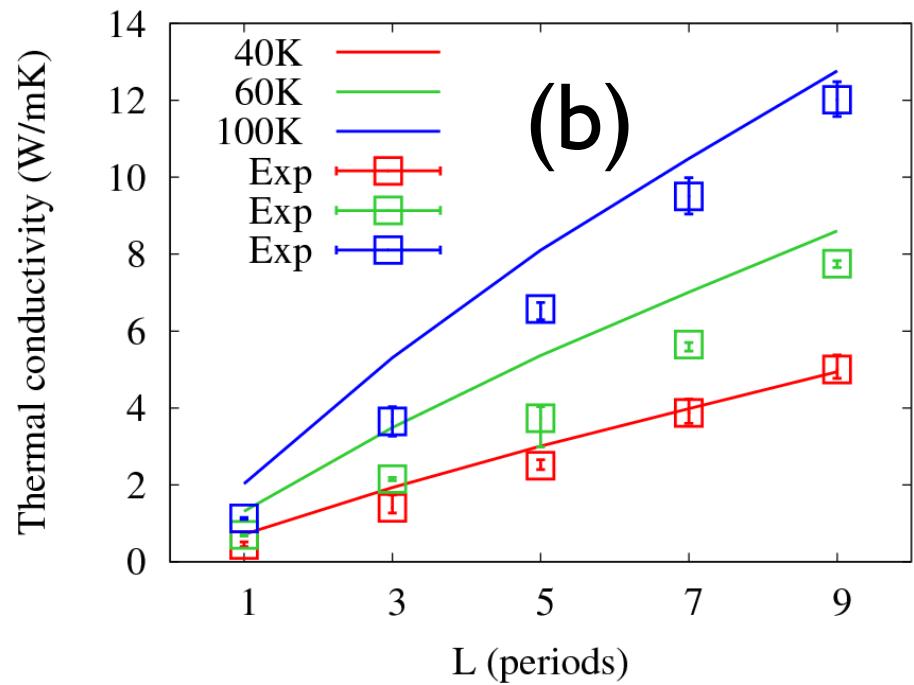
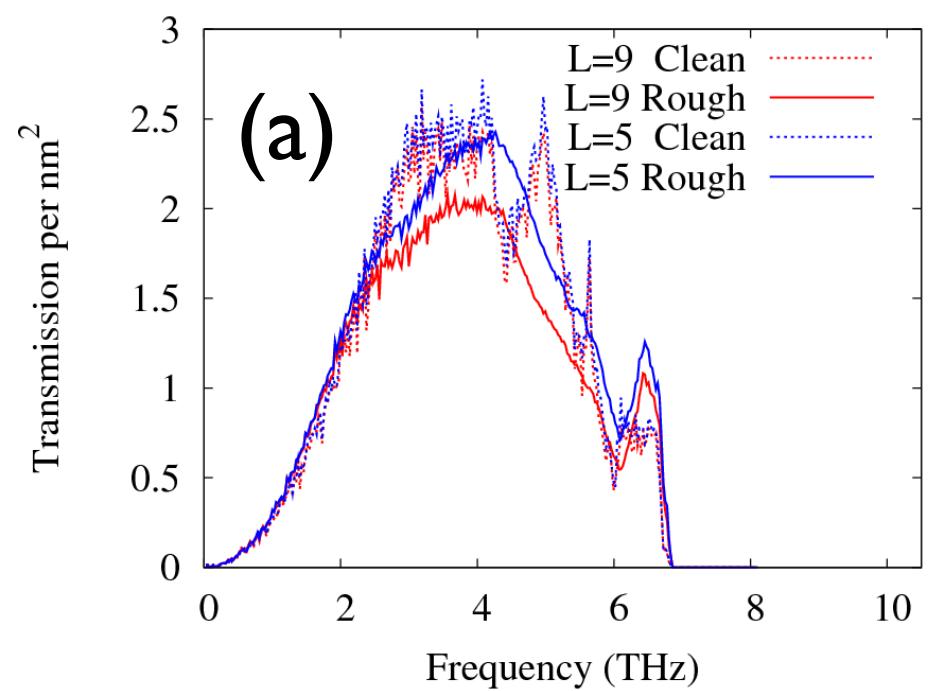


1 unit = 22 layers AlAs + 22 layers GaAs

Period length =  $2 * (22 * 5.4 \text{ Ang}) = 23.76 \text{ nm}$

N-periods ( $N=1,3,5,7,9$ ); 3x3 cross section  
for a total of 1584,...,up to 14256 atoms

# Transmission and Conductivity



# Conclusions

- The developed force field can be calculated for an arbitrary crystal structure
- It can be used to:
  - Do LD, get phonon spectra, lifetimes,  $\kappa$  (**fast**)
  - Do MD, get lifetimes and  $\kappa$  including alloy scattering and anharmonic effects **nonperturbatively**
  - Set up the GFs to calculate transmission & conductance
- LD faster and more accurate than GK-MD, but valid at low T
- In nanostructured materials:
  - Wave effects are important,
  - Heat transport can have a large ballistic component
  - Boundary scattering can be dominant
  - Optical modes contribution is increased

# Acknowledgements

- Gang Chen (MIT)
- Junichiro Shiomi (U Tokyo) ZrCoSb, PbTe
- Takuma Shiga (U Tokyo) PbTe
- Maria Luckyanova (MIT) GaAs/AlAs SLs
- J. Garg (MIT) GaAs/AlAs phonon lifetimes
- TF Luo (Notre Dame) GaAs